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Frustrated Spin System in θ-(BEDT-TTF)$_2$RbZn(SCN)$_4$

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The origin of the spin gap behavior in the low-temperature dimerized phase of θ-(BEDT-TTF)$_2$RbZn(SCN)$_4$ has been theoretically studied based on the Hartree-Fock approximation for the on-site Coulomb interaction at absolute zero. Calculations show that, in the parameter region considered to be relevant to this compound, antiferromagnetic ordering is stabilized between dimers consisting of pairs of molecules coupled with the largest transfer integral. Based on this result an effective localized spin 1/2 model is constructed which indicates the existence of the frustration among spins. This frustration may result in the formation of spin gap.

KEYWORDS: BEDT-TTF, spin gap, Hartree-Fock approximation, on-site Coulomb interaction, antiferromagnetic spin ordering, frustration

Two-dimensional (2D) organic conductors composed of BEDT-TTF (abbreviated as ET) have been attracting spread attention due to the variety of their electronic properties. In spite of the fact that the electron concentration of the conducting ET layer is fixed at 3/4 in compounds expressed as (ET)$_2X$, where X are anions, various phases such as paramagnetic metal, superconductor, paramagnetic insulator, antiferromagnetic (AF) insulator and even a spin-gapped (SG) insulator emerge. To understand these diverse behaviors, the role of Coulomb interaction is crucial because its value is considered to be of the order of the bandwidths in these compounds. Such effects of on-site Coulomb interaction have been investigated systematically by Kino and Fukuyama within the Hartree-Fock (HF) approximation for κ-(ET)$_2X$, α-(ET)$_2$I$_3$ and α-(ET)$_2M$Hg(SCN)$_4$.[1,2] It was shown by them that the ground state properties of κ-(ET)$_2X$ can be explained by considering each dimer as a unit[2] as was argued by Kanoda on experimental grounds.[3] The term 'dimer' denotes the pair of parallel molecules between whom the transfer integral is noticeably larger than the other transfer integrals. Hence the AF insulating phase of κ-(ET)$_2X$ is considered to be a Mott insulator due to the existence of one hole per dimer.[3,4]

Such theoretical procedures of combing the HF calculations and the quantum spin model so derived also allow us to understand the possible origin of the SG behavior in λ-(BETS)$_2$GaX_zY_{4-z}, whose donor is a seleno-analog molecule of ET, i.e. BETS (abbreviation for BEDT-TSeF).[5] The existence of a SG in this system had originally been suggested from magnetic susceptibility measurements,[6] and its origin was not due to the spin-Peierls (SP) transition. This compound has a dimeric structure similar to κ-(ET)$_2X$; the intradimer transfer integral is about twice that of the other transfer integrals. Thus the insulating phase can be considered as a 2D localized spin-1/2 system where each hole is localized on a dimer but an intrinsic alternation of the superexchange couplings between these spins exists, which may lead to the formation of SG.[5]

Recently another 2D organic compound θ-(ET)$_2$RbZn(SCN)$_4$ has been synthesized which shows a SG behavior.[7] The existence of a SG has been suggested from magnetic susceptibility[8,9] and NMR[10] measurements. The θ-type ET compounds in general have a donor structure with two ET molecules in a unit cell as shown in Fig. 1(a) and have a simple 3/4-filled band, that is, they do not have a dimeric structure. However, in the case of θ-(ET)$_2$RbZn(SCN)$_4$, when it is slowly cooled, a metal-insulator transition occurs at 190 K accompanied by a lattice modulation[9] which leads to the dimerization along the c-direction, thus the unit cell volume doubles and the transfer integrals become modulated as in Fig. 1(b). No SP lattice distortion has been observed so far[9] in the temperature range where the magnetic susceptibility shows a steep decrease. It can be seen in Fig. 1(b) that molecule pairs (1-3) and (2-4) with intradimer transfer integrals t_{p3} may be considered as dimers, but the value of t_{p3} is not so large as compared to the other transfer integrals. Since in organic conductors such as (TMTSF)$_2X$ and κ-(ET)$_2X$ the dimers consist of parallel molecules, we may even be able to consider the parallel (1-2) and (3-4) molecule pairs as dimers possessing an intradimer transfer integral t_{c1}.

The aim of this study is to elucidate whether dimers can be considered as units in the donor layer, and if it is so, which pairs of molecules should be considered as dimers. Furthermore, based on these results, the origin of the SG phenomenon will be investigated.

In order to theoretically study the electronic structure of the slowly cooled low temperature phase of θ-(ET)$_2$RbZn(SCN)$_4$, only its 2D donor plane (Fig. 1(b)) is considered where the transfer integrals between ET molecules are assumed as in Fig. 1(b) together with the

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on-site Coulomb interaction U on ET molecule. The Hamiltonian is given as follows;

$$H = \sum_{<i,j>} \sum_{\sigma} \left(t_{i,j} a^{\dagger}_{i\sigma} a_{j\sigma} + h.c. \right) + U \sum_{i} n_{i\uparrow} n_{i\downarrow}, \quad (1)$$

where $< i, j >$ denotes the neighboring site pair, σ is the spin index which takes $\uparrow$ and $\downarrow$, $n_{i\sigma}$ and $a^{\dagger}_{i\sigma}$ $(a_{i\sigma})$ denote the number operator and the creation (annihilation) operator for the electron of spin σ at the ith site, respectively.

The Coulomb interaction U is treated in the HF approximation in a manner similar to that in refs. 1 and 2. Our calculations are carried out at $T = 0$ and the average electron density is fixed at 3/4-filling, namely one hole per two ET molecules as in the real compound. Several types of AF solutions are taken into account as shown in Fig. 2 and their energies are compared as a function of U so that the true ground state is searched for. The total energy $\mathcal{E}$ is calculated as

$$\mathcal{E} = \frac{1}{N_{cell}} \sum_{lk\sigma} \epsilon_{lk\sigma} n_F \left(\epsilon_{lk\sigma} \right) - U \sum_{i} \langle n_{i\uparrow} \rangle \langle n_{i\downarrow} \rangle , \quad (2)$$

where N_{cell} is the total number of cells, $\epsilon_{lk\sigma}$ is the lth eigenvalue at each k and $n_F(\epsilon)$ is the Fermi distribution function. Due to the structure of interdimer transfer integrals which we will discuss later, 3 different types of AF (a),(b) and (c), as shown in Fig. 2 exist, where the spins within the pairs (1-3) and (2-4) are parallel and AF ordering occurs between the pairs. In the case of (d) type AF ordering, the spins within the (1-2) and (3-4) pairs are parallel and 2D AF ordering takes place between pairs.

The calculated energies of each state, α, relative to the paramagnetic solution, $\Delta E(\alpha) = E_\alpha - E_p$, for four different types of AF solutions are shown in Fig. 4. These results show that (a) and (b) types of AF, which are degenerate, are stabilized within realistic values of U, namely $U = 0.6 - 1.0$ eV. In these (a) and (b) types AF, the hole density on each ET molecule is similar but differs by a few percent from +0.5, and the magnitude of spin moments is $0.8 - 0.9\mu_B$ per dimer. Hence we can consider that the electrons are almost fully localized on each dimer.

From the above results, we shall consider the pairs (1-3) and (2-4) as dimers. As shown in refs. 2 and 5 the resulting dimer model can be constructed by estimating the superexchange couplings using the relation $J \simeq 4t^2/U_{dimer}$ (t is the effective interdimer transfer energy and U_{dimer} is the effective Coulomb interaction between two holes in a dimer), which is given in Fig. 3 with the magnitudes of $J_2 \simeq 0.21J_1$ and $J_3 \simeq 0.19J_1$. This estimate shows that J_1 is much larger than J_2 and J_3 is in accordance with the HF results where (a) or (b) type AF is stabilized.

The quantum fluctuations among spins are taken into account in this model. The phase diagram of the ground state of such a 2D spin-1/2 model on the plane of J_2/J_1 and J_3/J_1, can be deduced as in Fig. 5.[11] When $J_3 = 0$ ($J_2 = 0$), the model is identical to spin 1/2 chains coupled by nearest-neighbor interaction J_2 (J_3) and next-nearest-neighbor interaction J_1 which induces frustration between spins. In this model it is known[12] that when the ratio of the nearest-neighbor and the next-nearest-neighbor interaction, J_2/J_1 for $J_3 = 0$, for example, is increased, the low energy exitation changes its behavior from the one with a finite gap like the Majumdar-Ghosh model ($J_2/J_1 = 2$) to a gapless one like a Heisenberg chain at $J_2/J_1 = 1/\alpha_c; \alpha_c = 0.2411$[13] (see the axis in Fig. 5). Similar behavior exists on increasing J_3/J_1 at $J_2 = 0$. When $J_2 = J_3$ (the dot-dashed line in Fig. 5), the model reduces to a 2D AF Heisenberg model with nearest-neighbor coupling $J_2 = J_3$ and next-nearest-neighbor coupling J_1 along *only one* diagonal direction.[14] Its ground state is unknown except for the case of $J_1 = J_2 = J_3$, which is the simple triangular lattice with no SG.[15] This is approximately similar to the case of the dimer model for κ-$(ET)_2X$[1, 2] as shown in Fig. 5 and the ground state experimentally observed there is actually an AF insulator.[4] (2D Heisenberg model with nearest-neighbor and next-nearest-neighbor along *both* diagonal directions has been well studied.[16]) As seen in Fig. 5, θ-$(ET)_2RbZn(SCN)_4$ is located in the unexplored region, yet in this region frustration is large such that the ground state may have a SG. This is the possible explanation we propose in this paper.

Here we note that if θ-$(ET)_2RbZn(SCN)_4$ is in the region of AF, the SP transition will be a candidate for the origin of the SG behavior because J_1 is much larger than J_2 and J_3. It is known that the effect of interchain coupling on SP transition is to enhance the tendency toward AF long range order.[17] However, the competition between SP transition and Néel ordering in the presence of frustration among the interchain couplings is also an interesting unanswered question.

In SG systems, the impurity effect is interesting because impurities easily destroy the SG and induce AF long range order.[18] If some kind of disorder is introduced into θ-$(ET)_2RbZn(SCN)_4$ without any structural changes, the HF calculations predict that the configuration of the magnetic ordering will be either (a) or (b) type AF. In recent experiments in this direction, however, the dimeric structure was unfortunately not maintained; in θ-$(ET)_{2-x}(BMDT\text{-}TTF)_xRbZn(SCN)_4$ and θ-$(ET)_2Rb_{1-x}Cs_xZn(SCN)_4$, the structural phase transition observed in the pure compound is supressed and then the SG collapses.[19, 20]

In summary, the origin of the SG behavior in the slowly cooled dimerized phase in θ-$(ET)_2RbZn(SCN)_4$ is studied both by the HF calculations and the resulting effective dimer spin model. HF calculations indicate that the pairs of molecules coupled with the largest transfer integrals should be considered as dimers, and that the electrons are localized on each dimer due to the Coulomb interaction forming a Mott insulator. Quantum effect will create frustration among the localized spins which is the possible origin of the SG.

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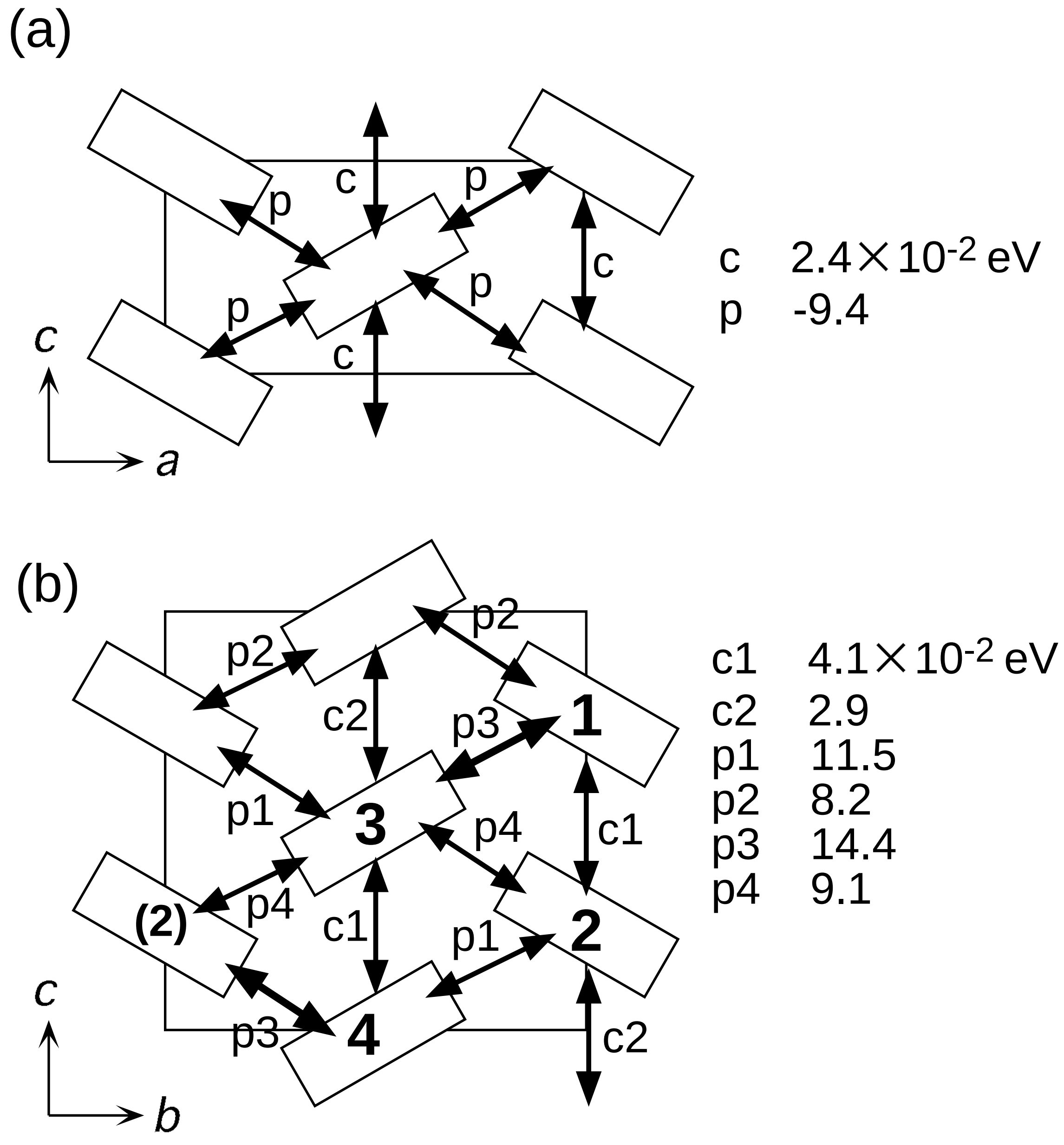
Fig. 1. Schematic donor structure of θ-(BEDT-TTF)$_2$RbZn(SCN)$_4$ in the high-temperature phase (a) and the slowly cooled low-temperature phase (b). Each ET molecule is schematically expressed as a rectangle. The values of transfer integrals are given by $t = Es$, where $E = -10$ eV and s is the value of the overlap integral taken from ref. 9.

Fig. 2. Different types of AF ordering for the structure given in Fig. 1. Circles and ellipses represent ET molecules and dimers, respectively. The magnetic unit cells are shown by rectangles.

Fig. 3. Effective dimer model for θ-$(\mathrm{ET})_2\mathrm{RbZn(SCN)}_4$. Full circles represent dimers and the values of the effective superexchange couplings are shown. Thick, thin and thin-dotted lines represent the spin exchange couplings, J_1, J_2 and J_3, respectively.

Fig. 4. Energy of each state, E_α, shown in Fig. 2 relative to that of the paramagnetic solution, E_p, $\Delta E(\alpha) = E_\alpha - E_p$.

Fig. 5. The schematic phase diagram of the Heisenberg spin model described in Fig. 3.[11)] It is symmetric with respect to the dot-dashed line. SG, nDAFH, TLAFH, AFLRO and MG represent spin gap, n-dimensional antiferromagnetic Heisenberg model, triangular lattice antiferromagnetic Heisenberg model, antiferromagnetic long range order and Majumdar-Ghosh point, respectively. The regions where a spin gap is known to exist are shown by the thick lines. The regions where θ-$(\mathrm{ET})_2\mathrm{RbZn(SCN)}_4$ and κ-$(\mathrm{ET})_2\mathrm{X}$ are expected to be located are shown by the shaded and the dotted areas, respectively.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c
p
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a
c 2.4×10^{-2} eV
p -9.4
(b)
p2
p2
c2
p3
1
p1
3
p4
c1
(2)
p4
c1
p1
2
p3
4
c2
c
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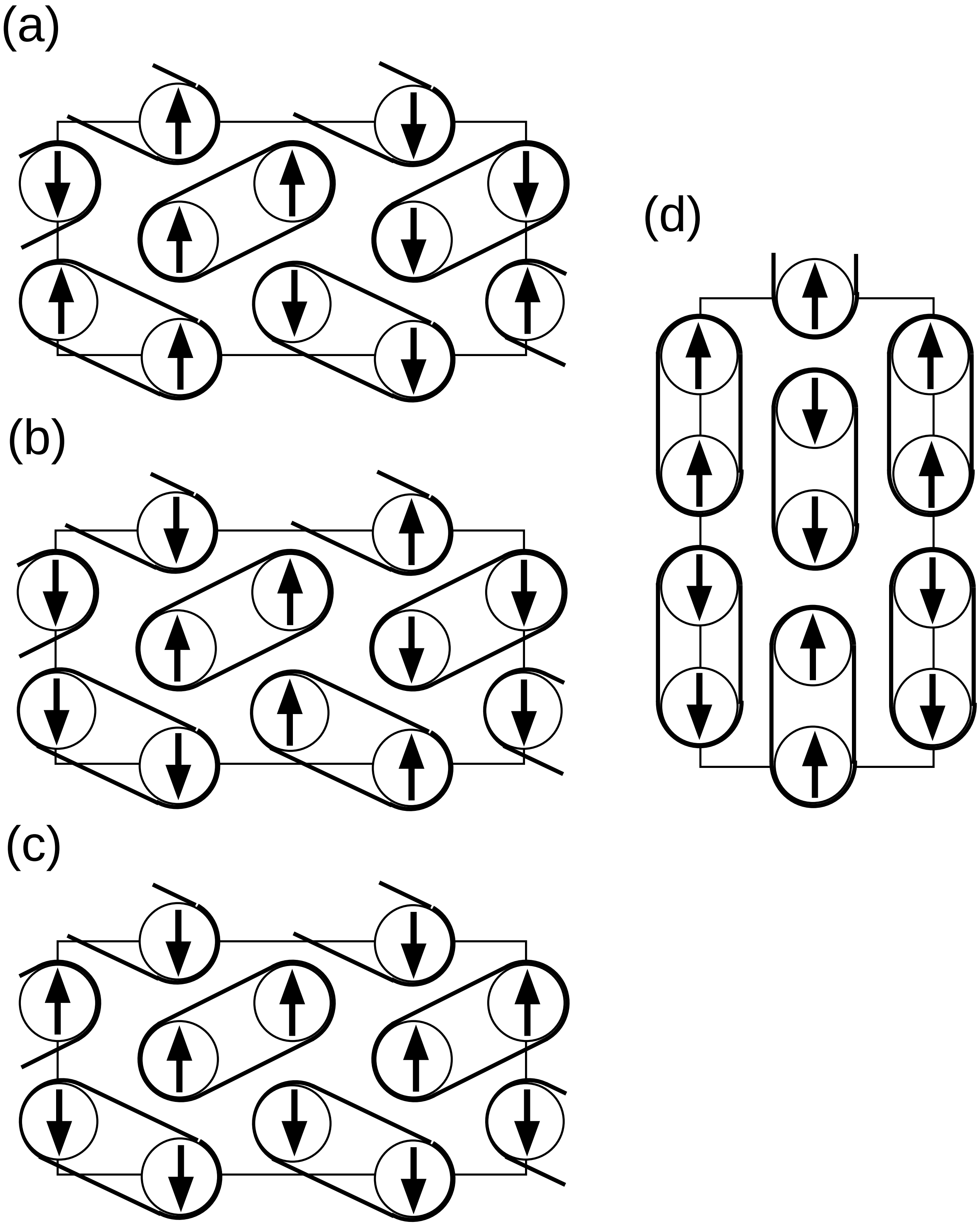
p4 9.1


(a)
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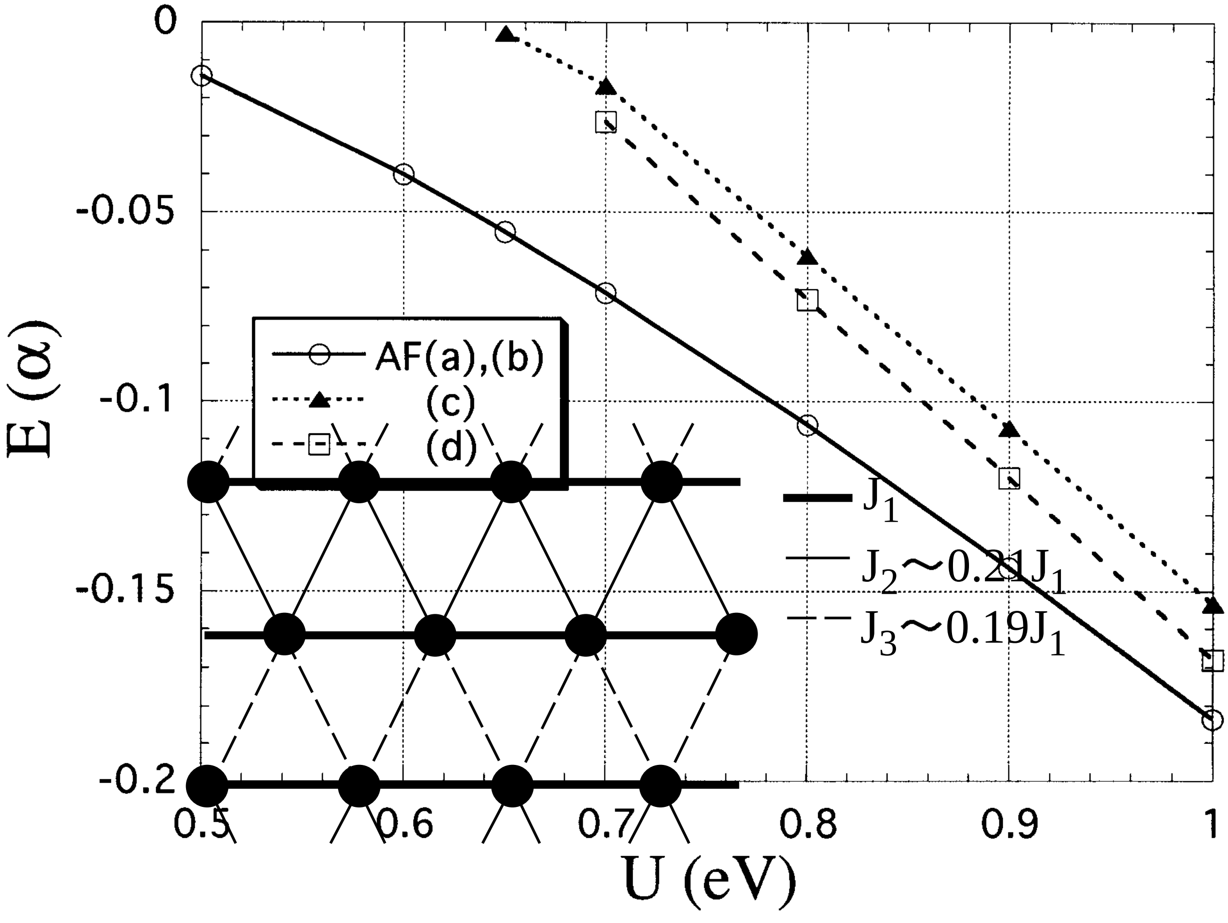
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U (eV)
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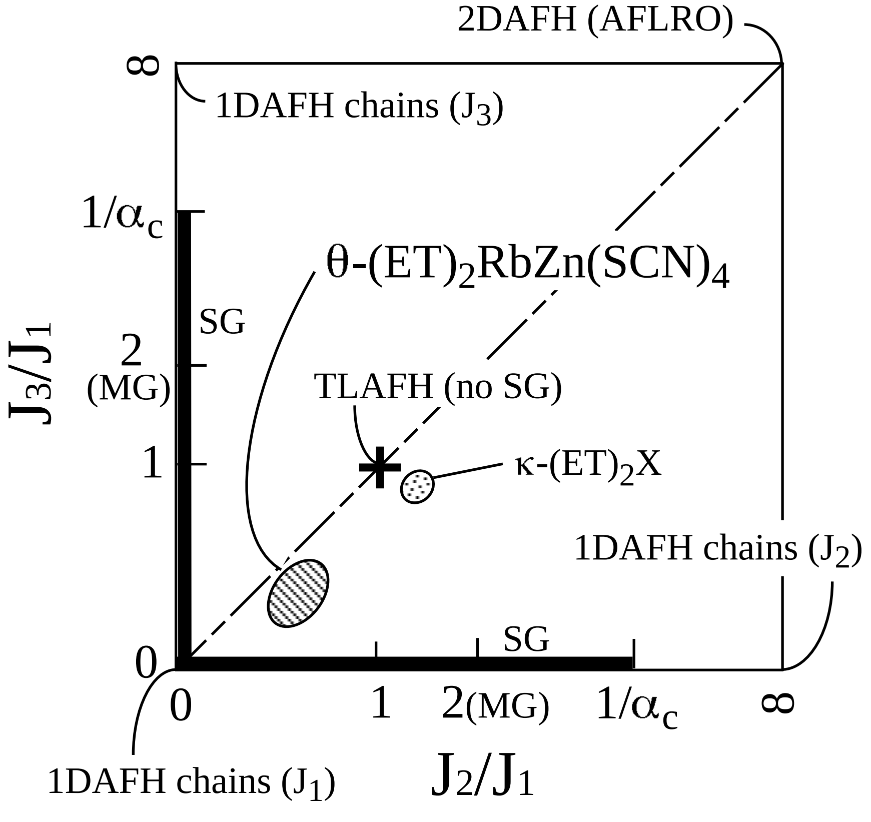
-0.1
-0.15
-0.2
0.5
0.6
0.7
0.8
0.9
1
AF(a),(b)
(c)
(d)
J_1
$J_2 \sim 0.21 J_1$
$J_3 \sim 0.19 J_1$



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∞
1DAFH chains (J_3)
$1/\alpha_c$
θ-(ET)$_2$RbZn(SCN)$_4$
SG
2
(MG)
TLAFH (no SG)
1
κ-(ET)$_2$X
1DAFH chains (J_2)
SG
0
0
1
2(MG)
$1/\alpha_c$
∞
1DAFH chains (J_1)
J_2/J_1
J_3/J_1